

Supplementary Materials for

Strain versus Tunable Terahertz Nanogap Width: A Simple Formula and a Trench below

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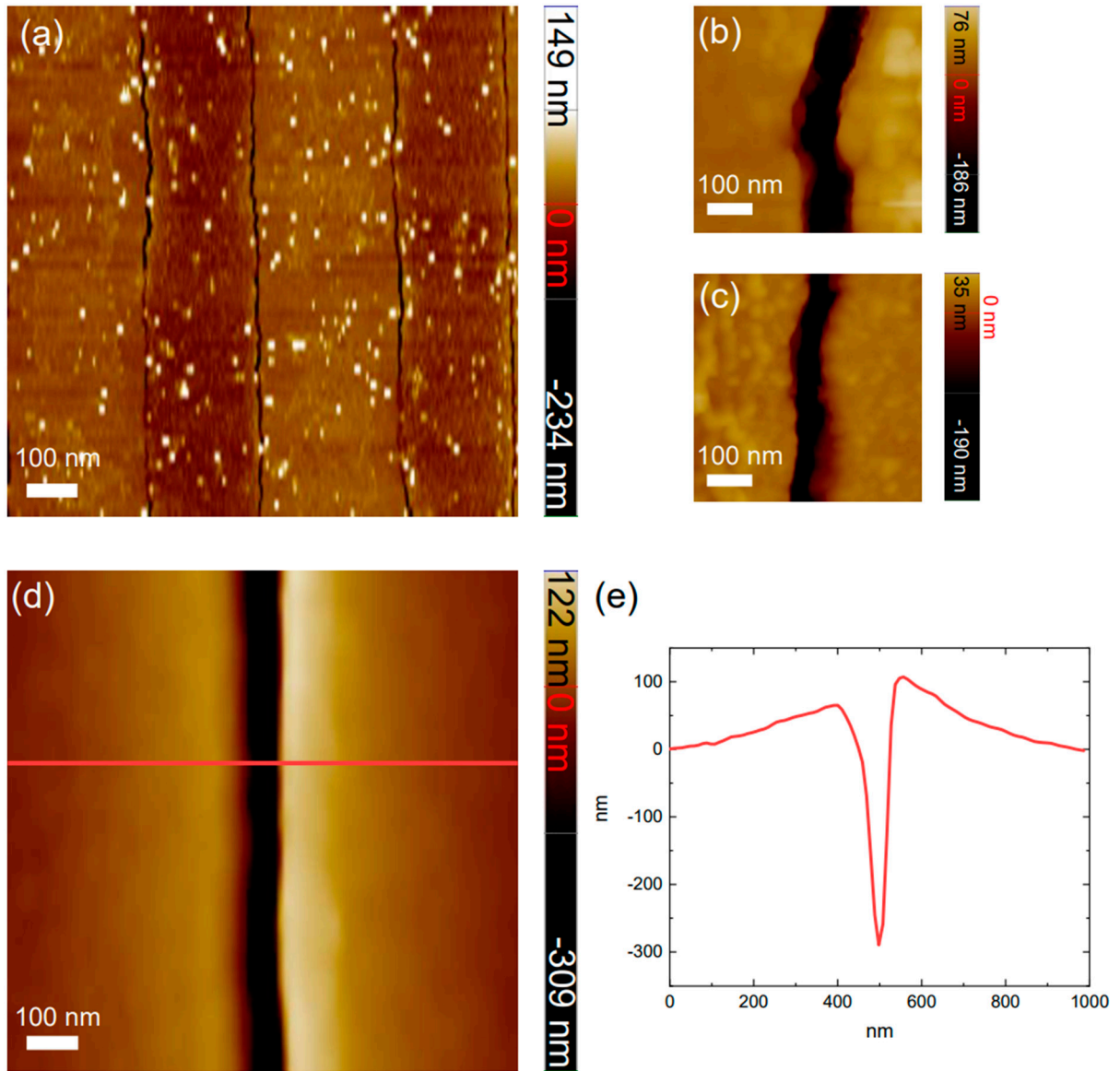


Figure S1. (a) shows the $20\ \mu\text{m} \times 20\ \mu\text{m}$ size topography zero-gap after etching the gold in 0 % strain. (b) is same topography Figure 2 (d). (c) depicts a close-up view of one of the trenches in (a). (d) shows the gold gap topography of the bent zero-gap in stage displacement $900\ \mu\text{m}$ (strain = 1.79 %). (e) is the line profile along the red line in (d).